

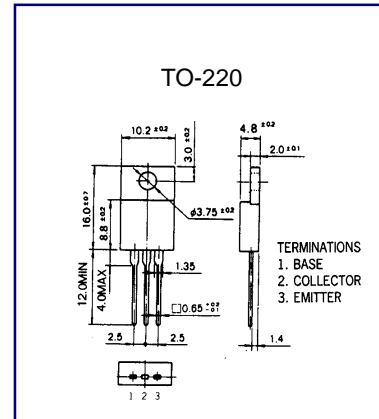


**2SD288**

**NPN EPITAXIAL SILICON TRANSISTOR**

**LOW FREQUENCY POWER AMPLIFIER**

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**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V <sub>CB0</sub>	8.0	V
Collector-Emitter Voltage	V <sub>CE0</sub>	55	V
Emitter-Base voltage	V <sub>EB0</sub>	5	V
Collector Current (DC)	I <sub>C</sub>	3	A
Collector Dissipation (T <sub>c</sub> =25°C)	P <sub>C</sub>	20	W
Junction Temperature	T <sub>j</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-50~150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C)**

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> = 50V , I <sub>E</sub> =0			50	μA
DC Current Gain	h <sub>FE1</sub>	V <sub>CE</sub> = 5V , I <sub>C</sub> =0.5A	40		240	V
Collector- Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =1A , I <sub>B</sub> =0.1A			1.0	
Current Gain Bandwidth Product						